# Vladimir Gavrilenko

## List of Publications by Year in Descending Order



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| 180 papers | 1,676 citations | 21 h-index | 31 g-index |
| 203 ext. papers | 2,056 ext. citations | 1.6 avg, IF | 4.22 L-index |

| # | Paper | IF | Citations |
|---|---|---|---|
| 180 | Generation of Terahertz Radiation in InP:Fe Crystals Due to Second-Order Lattice Nonlinearity. *Semiconductors*, **2021**, 55, 785 | 0.7 | |
| 179 | Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at ~6 μm wavelength from HgCdTe quantum wells. *Journal of Applied Physics*, **2021**, 130, 214302 | 2.5 | 1 |
| 178 | Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. *Laser Physics*, **2021**, 31, 015801 | 1.2 | 2 |
| 177 | Photothermal Ionization Spectroscopy of Mercury Vacancies in HgCdTe Epitaxial Films. *JETP Letters* , **2021**, 113, 402-408 | 1.2 | 0 |
| 176 | Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. *Journal of Applied Physics*, **2021**, 129, 133106 | 2.5 | 4 |
| 175 | Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. *Technical Physics Letters*, **2021**, 47, 154-157 | 0.7 | 1 |
| 174 | Feasibility of lasing in the GaAs Reststrahlen band with HgTe multiple quantum well laser diodes. *Journal Physics D: Applied Physics*, **2021**, 54, 175108 | 3 | 2 |
| 173 | Terahertz plasmons in doped HgTe quantum well heterostructures: dispersion, losses, and amplification. *Applied Optics*, **2021**, 60, 8991-8998 | 1.7 | 0 |
| 172 | Effect of Internal Optical Losses on the Generation of Mid-IR Stimulated Emission in Waveguide Heterostructures with HgCdTe/CdHgTe Quantum Wells. *Semiconductors*, **2021**, 55, 899-902 | 0.7 | |
| 171 | Terahertz Emission from HgCdTe QWs under Long-Wavelength Optical Pumping. *Journal of Infrared, Millimeter, and Terahertz Waves*, **2020**, 41, 750-757 | 2.2 | 2 |
| 170 | Specific Growth Features of Nanostructures for Terahertz Quantum Cascade Lasers and Their Physical Properties. *Semiconductors*, **2020**, 54, 1092-1095 | 0.7 | 2 |
| 169 | Investigation of Stimulated Emission from HgTe/CdHgTe Quantum-Well Heterostructures in the 35 μm Atmospheric Transparency Window. *Semiconductors*, **2020**, 54, 1365-1370 | 0.7 | |
| 168 | Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. *Optical Engineering*, **2020**, 60, | 1.1 | 2 |
| 167 | Effects of the Electron–Electron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. *JETP Letters*, **2020**, 112, 508-512 | 1.2 | 0 |
| 166 | Plasmon recombination in narrowgap HgTe quantum wells. *Journal of Physics Communications*, **2020**, 4, 115012 | 1.2 | 3 |
| 165 | Sub-terahertz FET detector with self-assembled Sn-nanothreads. *Journal Physics D: Applied Physics*, **2020**, 53, 075102 | 3 | 4 |
| 164 | Fundamental Limits to Far-Infrared Lasing in Auger-Suppressed HgCdTe Quantum Wells. *ACS Photonics*, **2020**, 7, 98-104 | 6.3 | 13 |

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| 163 | Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. *Semiconductors*, **2020**, 54, 1096-1102 | 0.7 | 0 |
| 162 | Calculation of Wave Functions of Resonant Acceptor States in Narrow-Gap CdHgTe Compounds. *Semiconductors*, **2020**, 54, 827-831 | 0.7 | 3 |
| 161 | Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. *JETP Letters*, **2020**, 111, 575-581 | 1.2 | 2 |
| 160 | Temperature limitations for stimulated emission in 34 μm range due to threshold and non-threshold Auger recombination in HgTe/CdHgTe quantum wells. *Applied Physics Letters*, **2020**, 117, 083103 | 3.4 | 8 |
| 159 | Continuous-Wave Stimulated Emission in the 10–14-μm Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. *Semiconductors*, **2020**, 54, 1371-1375 | 0.7 | 1 |
| 158 | Photoluminescence Spectra of InAs/GaInSb/InAs Quantum Wells in the Mid-Infrared Region. *Semiconductors*, **2020**, 54, 1119-1122 | 0.7 | |
| 157 | Balance-equation method for simulating terahertz quantum-cascade lasers using a wave-function basis with reduced dipole moments of tunnel-coupled states. *Quantum Electronics*, **2019**, 49, 913-918 | 1.8 | 8 |
| 156 | Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magnetospectroscopy of Semiconductor Structures. *Semiconductors*, **2019**, 53, 1217-1221 | 0.7 | 4 |
| 155 | Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. *Semiconductors*, **2019**, 53, 1266-1271 | 0.7 | 1 |
| 154 | Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd0.7Hg0.3Te QWs Near 14 μm. *Semiconductors*, **2019**, 53, 1154-1157 | 0.7 | 4 |
| 153 | Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. *JETP Letters*, **2019**, 109, 96-101 | 1.2 | 0 |
| 152 | Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. *JETP Letters*, **2019**, 109, 191-197 | 1.2 | 1 |
| 151 | Carrier Recombination, Long-Wavelength Photoluminescence, and Stimulated Emission in HgCdTe Quantum Well Heterostructures. *Physica Status Solidi (B): Basic Research*, **2019**, 256, 1800546 | 1.3 | 10 |
| 150 | Massless Dirac fermions in III-V semiconductor quantum wells. *Physical Review B*, **2019**, 99, | 3.3 | 6 |
| 149 | Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. *Condensed Matter*, **2019**, 4, 27 | 1.8 | 2 |
| 148 | Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. *JETP Letters*, **2019**, 109, 657-662 | 1.2 | 6 |
| 147 | Magneto-transport in inverted HgTe quantum wells. *Npj Quantum Materials*, **2019**, 4, | 5 | 9 |
| 146 | Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. *Semiconductors*, **2019**, 53, 1363-1366 | 0.7 | 2 |

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| 145 | Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. *Journal of Physics Condensed Matter*, **2019**, 31, 145501 | 1.8 | 10 |
| 144 | Chain of Dirac spectrum loops of nodes in crossed magnetic and electric fields. *Physical Review B*, **2018**, 97, | 3.3 | 4 |
| 143 | Stimulated emission in the 2.8-3.5 Ёh wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. *Optics Express*, **2018**, 26, 12755-12760 | 3.3 | 18 |
| 142 | Magnetooptical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. *Semiconductors*, **2018**, 52, 436-441 | 0.7 | |
| 141 | Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. *Journal of Experimental and Theoretical Physics*, **2018**, 127, 1125-1129 | 1 | 4 |
| 140 | Terahertz Injection Lasers Based on a PbSnSe Solid Solution with an Emission Wavelength up to 50 Ёh and Their Application in the Magnetospectroscopy of Semiconductors. *Semiconductors*, **2018**, 52, 1590-1594 | 0.7 | 7 |
| 139 | Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. *Semiconductors*, **2018**, 52, 1586-1589 | 0.7 | 5 |
| 138 | Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. *JETP Letters*, **2018**, 108, 329-334 | 1.2 | 2 |
| 137 | HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. *Journal of Physics: Conference Series*, **2018**, 1092, 012126 | 0.3 | |
| 136 | Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. *Sensors*, **2018**, 18, | 3.8 | 3 |
| 135 | Magnetooptics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. *Semiconductors*, **2018**, 52, 1386-1391 | 0.7 | 0 |
| 134 | Temperature Dependences of the Threshold Current and Output Power of a Quantum-Cascade Laser Emitting at 3.3 THz. *Semiconductors*, **2018**, 52, 1380-1385 | 0.7 | 8 |
| 133 | Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. *Journal of Physics Condensed Matter*, **2018**, 30, 495301 | 1.8 | 10 |
| 132 | Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. *Semiconductors*, **2018**, 52, 1375-1379 | 0.7 | 4 |
| 131 | Calculation of Multiply Charged States of Impurity-Defect Centers in Epitaxial Hg1 ⊠CdxTe Layers. *Semiconductors*, **2018**, 52, 1369-1374 | 0.7 | 4 |
| 130 | Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. *Physical Review B*, **2018**, 97, | 3.3 | 13 |
| 129 | Cyclotron resonance of dirac fermions in InAs/GaSb/InAs quantum wells. *Semiconductors*, **2017**, 51, 38-42 | 0.7 | 3 |
| 128 | Terahertz radiation generation in multilayer quantum-cascade heterostructures. *Technical Physics Letters*, **2017**, 43, 362-365 | 0.7 | 18 |

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| 127 | HgCdTe-based heterostructures for terahertz photonics. *APL Materials*, **2017**, 5, 035503 | 5.7 | 33 |
| 126 | Activation conductivity in HgTe/CdHgTe quantum wells at integer Landau level filling factors: Role of the random potential. *Semiconductors*, **2017**, 51, 1562-1570 | 0.7 | |
| 125 | On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. *Semiconductors*, **2017**, 51, 1531-1536 | 0.7 | 5 |
| 124 | Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5 □m. *Applied Physics Letters*, **2017**, 111, 192101 | 3.4 | 44 |
| 123 | Temperature-driven single-valley Dirac fermions in HgTe quantum wells. *Physical Review B*, **2017**, 96, | 3.3 | 23 |
| 122 | Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. *Semiconductor Science and Technology*, **2017**, 32, 095007 | 1.8 | 17 |
| 121 | Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. *Semiconductors*, **2017**, 51, 1557-1561 | 0.7 | 6 |
| 120 | Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs □hree-Layer□Gapless Quantum Wells. *JETP Letters*, **2017**, 106, 727-732 | 1.2 | 3 |
| 119 | Terahertz emission from CdHgTe/HgTe quantum wells with an inverted band structure. *Semiconductors*, **2016**, 50, 915-919 | 0.7 | 2 |
| 118 | Variation of the emission frequency of a terahertz quantum cascade laser. *Technical Physics Letters*, **2016**, 42, 230-233 | 0.7 | |
| 117 | Magnetospectroscopy of double HgTe/CdHgTe quantum wells. *Semiconductors*, **2016**, 50, 1532-1538 | 0.7 | 8 |
| 116 | Temperature-driven massless Kane fermions in HgCdTe crystals. *Nature Communications*, **2016**, 7, 12576 | 17.4 | 47 |
| 115 | Temperature-dependent magnetospectroscopy of HgTe quantum wells. *Physical Review B*, **2016**, 94, | 3.3 | 18 |
| 114 | Terahertz injection lasers based on PbSnSe alloy with an emission wavelength up to 46.5 □m. *Semiconductors*, **2016**, 50, 1669-1672 | 0.7 | 6 |
| 113 | Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2016**, 13, 534-537 | | 2 |
| 112 | Pressure- and temperature-driven phase transitions in HgTe quantum wells. *Physical Review B*, **2016**, 94, | 3.3 | 36 |
| 111 | Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. *Semiconductors*, **2016**, 50, 1651-1656 | 0.7 | 7 |
| 110 | Long wavelength stimulated emission up to 9.5 □m from HgCdTe quantum well heterostructures. *Applied Physics Letters*, **2016**, 108, 092104 | 3.4 | 25 |

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| 109 | Terahertz Response of Tightly Concatenated Two Dimensional InGaAs Field-Effect Transistors Integrated on a Single Chip. *International Journal of High Speed Electronics and Systems*, **2016**, 25, 1640012 | 0.5 | |
| 108 | Mercury vacancies as divalent acceptors in Hg y Te1 −y /Cd x Hg1 −x Te structures with quantum wells. *Semiconductors*, **2016**, 50, 1662-1668 | 0.7 | 5 |
| 107 | Terahertz imaging of Landau levels in HgTe-based topological insulators. *Applied Physics Letters*, **2016**, 108, 262102 | 3.4 | 8 |
| 106 | The study of the laser characteristics based on solid solution Pb1-xSnxSe (x ~ 0.07) emitting at spectral range of 16 μm. *Journal of Physics: Conference Series*, **2016**, 740, 012005 | 0.3 | |
| 105 | Exchange enhancement of the electron g factor in strained InGaAs/InP heterostructures. *Semiconductors*, **2015**, 49, 191-198 | 0.7 | 4 |
| 104 | Effect of the direct capture of holes with the emission of optical phonons on impurity-photoconductivity relaxation in p-Si:B. *Semiconductors*, **2015**, 49, 187-190 | 0.7 | 4 |
| 103 | Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. *JETP Letters*, **2015**, 100, 790-794 | 1.2 | 23 |
| 102 | Long wavelength superluminescence from narrow gap HgCdTe epilayer at 100 K. *Applied Physics Letters*, **2015**, 107, 042105 | 3.4 | 11 |
| 101 | Infrared magneto-spectroscopy of two-dimensional and three-dimensional massless fermions: A comparison. *Journal of Applied Physics*, **2015**, 117, 112803 | 2.5 | 5 |
| 100 | Effect of electron-electron interaction on cyclotron resonance in high-mobility InAs/AlSb quantum wells. *Journal of Applied Physics*, **2015**, 117, 112813 | 2.5 | 15 |
| 99 | Effective third-order nonlinearities in metallic refractory titanium nitride thin films. *Optical Materials Express*, **2015**, 5, 2395 | 2.6 | 40 |
| 98 | Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. *Semiconductors*, **2015**, 49, 1627-1633 | 0.7 | 5 |
| 97 | Long-wavelength injection lasers based on Pb1−x Sn x Se alloys and their use in solid-state spectroscopy. *Semiconductors*, **2015**, 49, 1623-1626 | 0.7 | 13 |
| 96 | Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. *Selected Topics in Electornics and Systems*, **2015**, 31-53 | 0 | 0 |
| 95 | Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. *Applied Physics Letters*, **2015**, 107, 152101 | 3.4 | 10 |
| 94 | Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. *Journal of Physics: Conference Series*, **2015**, 647, 012008 | 0.3 | 3 |
| 93 | Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. *Semiconductors*, **2015**, 49, 1611-1615 | 0.7 | 5 |
| 92 | Impurity-induced photoconductivity of narrow-gap Cadmium–Mercury–Telluride structures. *Semiconductors*, **2015**, 49, 1605-1610 | 0.7 | 6 |

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| 91 | Cyclotron resonance in InAs/AlSb quantum wells in magnetic fields up to 45 T. *Semiconductors*, **2015**, 49, 1616-1622 | 0.7 | |
| 90 | Detection of Terahertz Radiation by Dense Arrays of InGaAs Transistors. *International Journal of High Speed Electronics and Systems*, **2015**, 24, 1550002 | 0.5 | 4 |
| 89 | Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. *Nature Physics*, **2014**, 10, 233-238 | 16.2 | 143 |
| 88 | Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26 □m. *Applied Physics Letters*, **2014**, 104, 072102 | 3.4 | 28 |
| 87 | Time resolved photoluminescence spectroscopy of narrow gap Hg1□CdxTe/CdyHg1□Te quantum well heterostructures. *Applied Physics Letters*, **2014**, 105, 022102 | 3.4 | 23 |
| 86 | Terahertz detector with series connection of asymmetric gated transistors. *Journal of Physics: Conference Series*, **2014**, 486, 012016 | 0.3 | |
| 85 | Detection of terahertz radiation by tightly concatenated InGaAs field-effect transistors integrated on a single chip. *Applied Physics Letters*, **2014**, 104, 163508 | 3.4 | 6 |
| 84 | Specific features of the spectra and relaxation kinetics of long-wavelength photoconductivity in narrow-gap HgCdTe epitaxial films and heterostructures with quantum wells. *Semiconductors*, **2013**, 47, 1438-1441 | 0.7 | 15 |
| 83 | Magnetoabsorption in narrow-gap HgCdTe epitaxial layers in the terahertz range. *Semiconductors*, **2013**, 47, 1545-1550 | 0.7 | 5 |
| 82 | Relaxation kinetics of impurity photoconductivity in p-Si:B with various levels of doping and degrees of compensation in high electric fields. *Semiconductors*, **2013**, 47, 1461-1464 | 0.7 | 3 |
| 81 | Rashba spin splitting and cyclotron resonance in strained InGaAs/InP heterostructures with a two-dimensional electron gas. *Semiconductors*, **2013**, 47, 1485-1491 | 0.7 | 7 |
| 80 | Type II□type I conversion of GaAs/GaAsSb heterostructure energy spectrum under optical pumping. *Journal of Applied Physics*, **2013**, 113, 163107 | 2.5 | 13 |
| 79 | Cyclotron resonance in HgCdTe-based heterostructures in strong magnetic fields. *Journal of Physics: Conference Series*, **2013**, 461, 012038 | 0.3 | 1 |
| 78 | Spin-wave excitations and electron spin resonance in symmetric and asymmetric narrow-gap quantum wells. *Physical Review B*, **2013**, 87, | 3.3 | 14 |
| 77 | Spectra and kinetics of THz photoconductivity in narrow-gap Hg1□CdxTe (xSemiconductor Science and Technology, **2013**, 28, 125007 | 1.8 | 21 |
| 76 | Effects of Rashba spin splitting and exchange interaction in electron spin resonance in narrow-gap quantum well heterostructures. *Journal of Physics: Conference Series*, **2013**, 456, 012021 | 0.3 | 1 |
| 75 | Exchange enhancement of quasiparticle and ESR spin-gap in symmetric and asymmetric narrow-gap quantum wells. *Journal of Physics: Conference Series*, **2013**, 461, 012037 | 0.3 | |
| 74 | Cyclotron resonance in HgTe/CdTe(013) narrowband heterostructures in quantized magnetic fields. *JETP Letters*, **2012**, 95, 406-410 | 1.2 | 11 |

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| 73 | Cyclotron resonance in HgTe/CdTe-based heterostructures in high magnetic fields. *Nanoscale Research Letters*, **2012**, 7, 534 | 5 | 39 |
| 72 | Cyclotron resonance study in InAs/AlSb quantum well heterostructures with two occupied electronic subbands. *Journal of Applied Physics*, **2012**, 111, 093711 | 2.5 | 14 |
| 71 | Study of lifetimes and photoconductivity relaxation in heterostructures with Hg x Cd1 x Te/Cd y Hg1 y Te quantum wells. *Semiconductors*, **2012**, 46, 1362-1366 | 0.7 | 27 |
| 70 | Determination of the heterojunction type in structures with GaAsSb/GaAs quantum wells with various antimony fractions by optical methods. *Semiconductors*, **2012**, 46, 1376-1380 | 0.7 | 3 |
| 69 | Features of impurity-photoconductivity relaxation in boron-doped silicon. *Semiconductors*, **2012**, 46, 1387-1391 | 0.7 | 12 |
| 68 | Features of the persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells and a tunneling-transparent barrier. *Semiconductors*, **2012**, 46, 1396-1401 | 0.7 | 17 |
| 67 | Diagnostics of quantum cascade structures by optical methods in the near infrared region. *Semiconductors*, **2012**, 46, 1411-1414 | 0.7 | 2 |
| 66 | Rashba spin splitting and exchange enhancement of the g factor in InAs/AlSb heterostructures with a two-dimensional electron gas. *Semiconductors*, **2012**, 46, 1163-1170 | 0.7 | 18 |
| 65 | Exchange interaction effects in electron spin resonance: Larmor theorem violation in narrow-gap quantum well heterostructures. *Journal of Physics Condensed Matter*, **2012**, 24, 252201 | 1.8 | 7 |
| 64 | Experimental study of frequency multipliers based on a GaAs/AlAs semiconductor superlattices in the terahertz frequency range. *Semiconductors*, **2012**, 46, 121-125 | 0.7 | 35 |
| 63 | Studying the frequency tuning of pulsed terahertz quantum cascade lasers. *Radiophysics and Quantum Electronics*, **2012**, 54, 609-615 | 0.7 | 4 |
| 62 | The effect of exchange interaction on quasiparticle Landau levels in narrow-gap quantum well heterostructures. *Journal of Physics Condensed Matter*, **2012**, 24, 135601 | 1.8 | 7 |
| 61 | Theory of g-factor enhancement in narrow-gap quantum well heterostructures. *Journal of Physics Condensed Matter*, **2011**, 23, 385601 | 1.8 | 17 |
| 60 | High-responsivity terahertz detection by on-chip InGaAs/GaAs field-effect-transistor array. *Applied Physics Letters*, **2011**, 98, 153504 | 3.4 | 38 |
| 59 | Cyclotron resonance and interband optical transitions in HgTe/CdTe(0 1 3) quantum well heterostructures. *Semiconductor Science and Technology*, **2011**, 26, 125011 | 1.8 | 37 |
| 58 | Electron-electron interaction and spin-orbit coupling in InAs/AlSb heterostructures with a two-dimensional electron gas. *Semiconductors*, **2011**, 45, 110-117 | 0.7 | 20 |
| 57 | Relaxation of the impurity photoconductivity inp-Ge/Ge1 Sixquantum well heterostructures. *Semiconductor Science and Technology*, **2011**, 26, 085009 | 1.8 | 4 |
| 56 | Spin splitting in HgTe/CdHgTe (013) quantum well heterostructures. *JETP Letters*, **2010**, 92, 63-66 | 1.2 | 20 |

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| 55 | Terahertz spectroscopy of quantum-well narrow-bandgap HgTe/CdTe-based heterostructures. *JETP Letters*, **2010**, 92, 756-761 | 1.2 | 24 |
| 54 | GaAsSb/GaAs strained structures with quantum wells for lasers with emission wavelength near 1.3 μm. *Semiconductors*, **2010**, 44, 405-412 | 0.7 | 19 |
| 53 | Persistent photoconductivity in InAs/AlSb heterostructures with double quantum wells. *Semiconductors*, **2010**, 44, 616-622 | 0.7 | 23 |
| 52 | Terahertz emission and photoconductivity in n-type GaAs/AlGaAs quantum wells: the role of resonant impurity states. *Semiconductors*, **2010**, 44, 1394-1397 | 0.7 | 9 |
| 51 | High-resolution emission spectra of pulsed terahertz quantum-cascade lasers. *Semiconductors*, **2010**, 44, 1467-1471 | 0.7 | 3 |
| 50 | Kinetics of terahertz photoconductivity in p-Ge under impurity breakdown conditions. *Semiconductors*, **2010**, 44, 1476-1479 | 0.7 | 9 |
| 49 | The cyclotron resonance of holes in InGaAs/GaAs heterostructures with quantum wells in quantizing magnetic fields. *Semiconductors*, **2010**, 44, 1492-1494 | 0.7 | 6 |
| 48 | Wide-aperture detector of terahertz radiation based on GaAs/InGaAs transistor structure with large-area slit grating gate. *Technical Physics Letters*, **2010**, 36, 365-368 | 0.7 | 8 |
| 47 | Cyclotron Resonance of Extremely Conductive 2D Holes in High Ge Content Strained Heterostructures. *Journal of Low Temperature Physics*, **2010**, 159, 216-221 | 1.3 | 4 |
| 46 | High-field splitting of the cyclotron resonance absorption in strained p-InGaAs/GaAs quantum wells. *Physical Review B*, **2009**, 79, | 3.3 | 14 |
| 45 | Impurity breakdown and terahertz luminescence in n-GaN epilayers under external electric field. *Journal of Applied Physics*, **2009**, 106, 123523 | 2.5 | 21 |
| 44 | Emission spectra of terahertz quantum cascade laser. *Radiophysics and Quantum Electronics*, **2009**, 52, 494-499 | 0.7 | 2 |
| 43 | Fano resonances in the impurity photocurrent spectra of GaAs samples and an InGaAs/GaAsP quantum-well heterostructure doped with shallow acceptors. *Journal of Experimental and Theoretical Physics*, **2009**, 109, 466-471 | 1 | 3 |
| 42 | Difference-frequency generation in a butt-join diode laser. *Semiconductors*, **2009**, 43, 208-211 | 0.7 | 4 |
| 41 | Evolution of the photoresponse time of the GaAs/AlGaAs cyclotron resonance quantum Hall effect detector. *Semiconductors*, **2009**, 43, 223-227 | 0.7 | |
| 40 | Resonance detection of terahertz radiation in submicrometer field-effect GaAs/AlGaAs transistors with two-dimensional electron gas. *Semiconductors*, **2009**, 43, 528-531 | 0.7 | 2 |
| 39 | Relaxation of THz impurity photoconductivity in GaAs/InGaAsP and Ge/GeSi quantum well heterostructures. *Journal of Physics: Conference Series*, **2009**, 193, 012087 | 0.3 | |
| 38 | Impurity photoconductivity in strained p-InGaAs/GaAsP heterostructures. *JETP Letters*, **2008**, 88, 197-200 | 1.2 | |

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| 37 | Room-temperature intracavity difference-frequency generation in butt-joint diode lasers. *Applied Physics Letters*, **2008**, 92, 021122 | 3.4 | 17 |
| 36 | Magnetic field dependence of the photoresponse time of GaAs/AlGaAs quantum Hall effect device. *Semiconductor Science and Technology*, **2008**, 23, 095014 | 1.8 | 1 |
| 35 | Exchange enhancement of the g factor in InAs/AlSb heterostructures. *Semiconductors*, **2008**, 42, 828-833 | 0.7 | 31 |
| 34 | Fano resonance in the impurity photoconductivity spectrum of InP doped with shallow donors. *Physics of the Solid State*, **2008**, 50, 1211-1214 | 0.8 | 3 |
| 33 | Experimental study of nonlinear mode mixing in dual-wavelength semiconductor lasers. *Laser Physics*, **2007**, 17, 684-687 | 1.2 | 1 |
| 32 | Electron transport and detection of terahertz radiation in a GaN/AlGaN submicrometer field-effect transistor. *Semiconductors*, **2007**, 41, 232-234 | 0.7 | 21 |
| 31 | A multifrequency interband two-cascade laser. *Semiconductors*, **2007**, 41, 1209-1213 | 0.7 | 4 |
| 30 | Frequency shift in a system of two laser diodes. *Semiconductors*, **2007**, 41, 1364-1368 | 0.7 | 1 |
| 29 | Study of interband cascade lasers with tunneling transition. *Bulletin of the Russian Academy of Sciences: Physics*, **2007**, 71, 96-99 | 0.4 | |
| 28 | Generation of self-sustained pulsations of radiation in InGaAs/GaAs/InGaP quantum-well lasers. *Journal of Applied Spectroscopy*, **2007**, 74, 589-593 | 0.7 | |
| 27 | Fano resonance study in impurity photocurrent spectra of bulk GaAs and GaAs quantum wells doped with shallow donors. *Physical Review B*, **2007**, 75, | 3.3 | 8 |
| 26 | Nonlinear mode mixing in dual-wavelength semiconductor lasers with tunnel junctions. *Applied Physics Letters*, **2007**, 90, 171106 | 3.4 | 13 |
| 25 | Spectra of persistent photoconductivity in InAs/AlSb quantum-well heterostructures. *Semiconductors*, **2005**, 39, 22 | 0.7 | 15 |
| 24 | Current oscillations under lateral transport in GaAs/InGaAs quantum well heterostructures. *Semiconductors*, **2005**, 39, 44 | 0.7 | 4 |
| 23 | Cyclotron resonance in doped and undoped InAs/AlSb heterostructures with quantum wells. *Semiconductors*, **2005**, 39, 62 | 0.7 | 15 |
| 22 | Observation of the middle-infrared emission from semiconductor lasers generating two frequency lines in the near-infrared region of the spectrum. *Semiconductors*, **2005**, 39, 139 | 0.7 | |
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